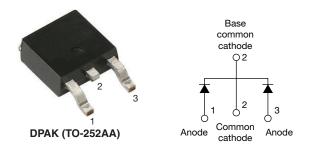
Vishay Semiconductors

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Hyperfast Rectifier, 2 x 4 A FRED Pt[®]



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 4 A				
V _R	200 V				
V _F at I _F	0.95 V				
t _{rr} (typ.)	23 ns				
T _J max.	175 °C				
Package	DPAK (TO-252AA)				
Circuit configuration	Common cathode				

FEATURES

- Hyperfast recovery time
- 175 °C max. operating junction temperature
- Output rectification freewheeling
- · Low forward voltage drop reduced Qrr and soft recovery
- Low leakage current
- AEC-Q101 gualified
- Meets JESD 201 class 1A whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		200	V			
Average rectified forward current	I _{F(AV)}	T _C = 164 °C	8	А			
Non-repetitive peak surge current per leg	I _{FSM}	$T_J = 25 \ ^{\circ}C$	80	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
		$I_F = 4 A$	-	0.87	0.95		
Forward voltage per leg V _F	M	I _F = 8 A	-	0.95	1.10		
	۷F	I _F = 4 A, T _J = 150 °C	-	0.71	0.80		
		I _F = 8 A, T _J = 150 °C	-	0.8	1.0		
		$V_{R} = V_{R}$ rated	-	-	4		
Reverse leakage current per leg	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$		-	40	μA	
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	80		
Junction capacitance per leg	CT	V _R = 200 V - 1		17	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	

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FREE



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 1 \text{ A}$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		23	27		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	20	-	ns A	
		T _J = 125 °C	$I_F = 4 A$	-	27	-		
Pools receivers ourrent		T _J = 25 °C		-	2	-		
Peak recovery current	IRRM	T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 160 V	-	3.4	-		
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	20	-	nC	
		T _J = 125 °C	Ĩ	-	46	-		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage range	e temperature	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance,	per leg	R _{thJC}		-	2.7	3.2	°C/W
junction to case	per device	nthJC		-	1.35	1.6	0/10
Approximate weight					0.3		g
Approximate weight					0.01		oz.
Marking device			Case style DPAK (TO-252AA)	8CWH02FNH			



VS-8CWH02FNHM3

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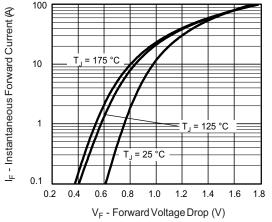


Fig. 1 - Typical Forward Voltage Drop Characteristics

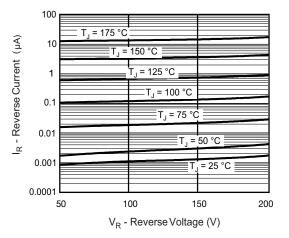


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

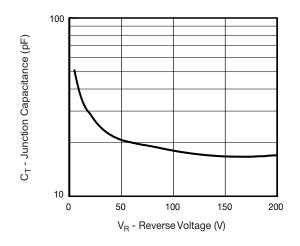
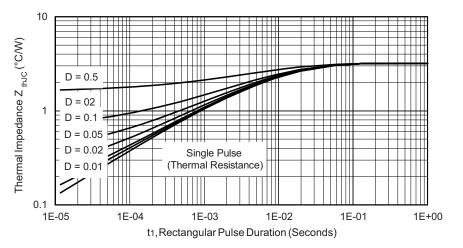


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage







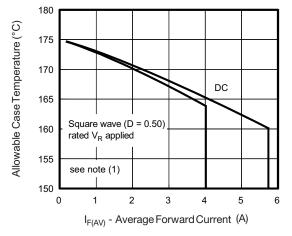


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

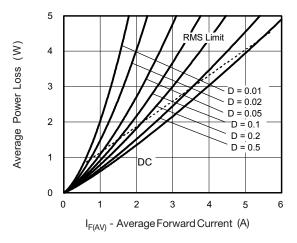


Fig. 6 - Forward Power Loss Characteristics

Note

- Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); (1)
- Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 D)$; I_R at V_{R1} = rated V_R



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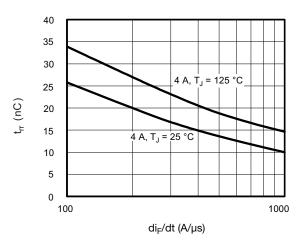


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

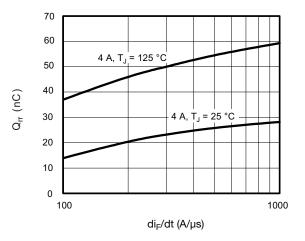


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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VS-8CWH02FNHM3



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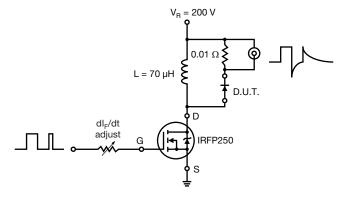


Fig. 9 - Reverse Recovery Parameter Test Circuit

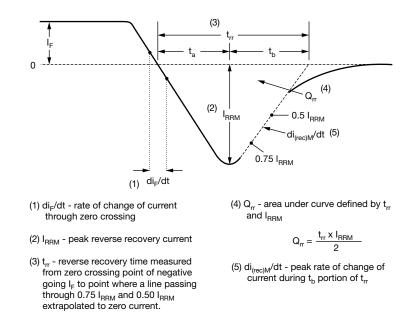


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

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Device code	vs-	8	с	w	н	02	FN	TRL	Н	М3
	1	2	3	4	5	6	7	8	9	10
		 Vishay Semiconductors product Current rating (8 = 8 A) Circuit configuration: C = Common cathode 								
	4	- Pac	C = Common cathode Package identifier: W = D-PAK							
	6	- Vol		ast reco ng (02 = 52AA	-)				
			 None = Tube TR = Tape and reel 							
	9	• TI	 TRL = Tape and reel (left oriented) TRR = Tape and reel (right oriented) H = AEC-Q101 qualified 							
	10	- Env	ironmer	ntal digit	:	complia	nt, and	termina	tions lea	ad (Pb)-

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-8CWH02FNHM3	75	Antistatic plastic tube					
VS-8CWH02FNTRHM3	2000	13" diameter reel					
VS-8CWH02FNTRRHM3	3000	13" diameter reel					
VS-8CWH02FNTRLHM3	3000	13" diameter reel					

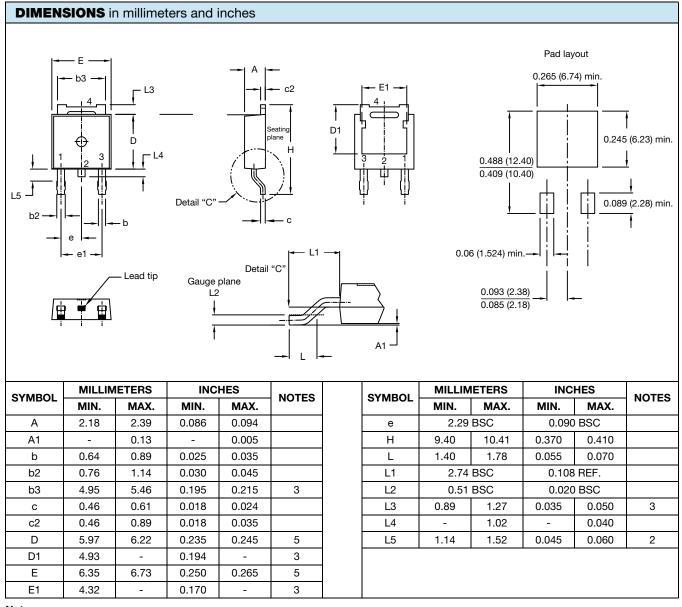
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95519				
Part marking information	www.vishay.com/doc?95518				
Packaging information	www.vishay.com/doc?95033				

Outline Dimensions



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DPAK (TO-252AA)



Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Dimensions D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁵⁾ Outline conforms to JEDEC[®] outline TO-252AA, except for D1 dimension



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